

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A memory cell comprising:

a first electrode ~~deposited on~~ over a substrate body;

a second electrode, wherein the first electrode and the second electrode provide electrical access to ~~the~~ a memory cell body;

Ver ~~a first layer of a silver chalcogenide layer~~ disposed between the first electrode and the second electrode, where the ^{*silver chalcogenide*} ~~first~~ layer forms a first portion of a the memory cell body; and

~~a second layer of a rigid chalcogenide glass layer, that forms a second portion of the memory cell body,~~ wherein the ~~second rigid chalcogenide glass~~ layer is also disposed between the first electrode and the second electrode and forms a second portion of the memory cell body, wherein the rigid chalcogenide glass permits comprises silver chalcogenide material from said silver chalcogenide layer in an amount such that a conductive pathway to can form ~~between the first electrode and the second electrode in said rigid chalcogenide glass layer~~ in response to an electric potential applied between the first electrode and the second electrode.

2. (Currently Amended) The memory cell ~~as defined in~~ of Claim 1, wherein ~~the first layer of the silver chalcogenide layer~~ is formed directly on the first electrode.